

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

# GT10J312, GT10J312(SM)

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

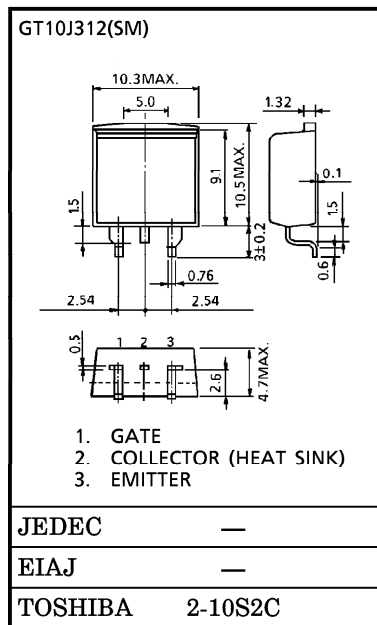
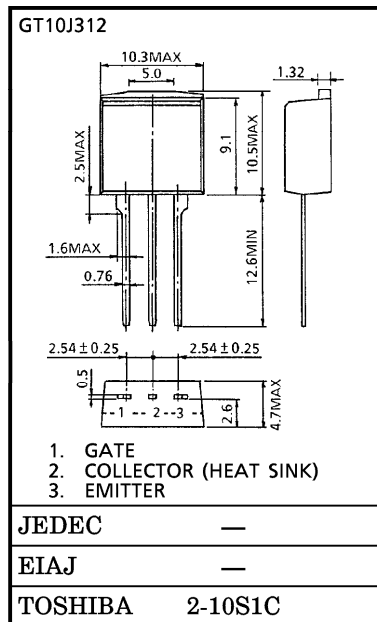
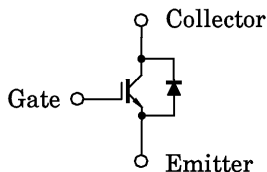
Unit in mm

- The 3rd Generation
- Enhancement-Mode
- High Speed :  $t_f=0.30\mu s$  (Max.)
- Low Saturation Voltage :  $V_{CE(sat)}=2.7V$  (Max.)
- FRD included between Emitter and Collector.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	$V_{CES}$	600	V
Gate-Emitter Voltage	$V_{GES}$	$\pm 20$	V
Collector Current	DC	$I_C$	10 A
	1ms	$I_{CP}$	20 A
Emitter-Collector Forward Current	DC	$I_F$	10 A
	1ms	$I_{FM}$	20 A
Collector Power Dissipation (Tc = 25°C)	$P_C$	60	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

EQUIVALENT CIRCUIT



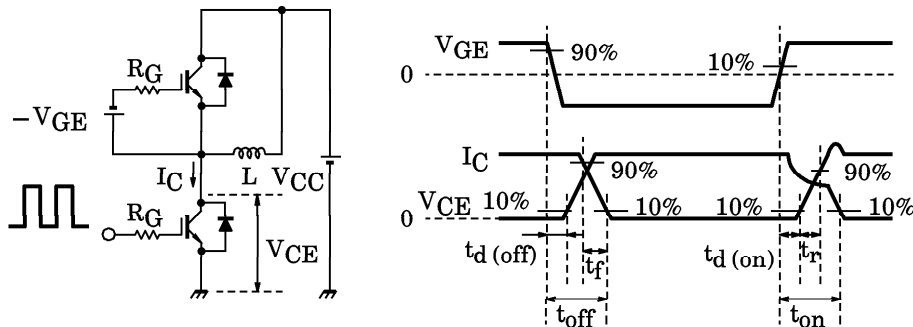
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GES}$	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector Cut-Off Current	$I_{CES}$	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-Off Voltage	$V_{GE(OFF)}$	$I_C = 1mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10A, V_{GE} = 15V$	—	2.1	2.7	V
Input Capacitance	$C_{ies}$	$V_{CE} = 20V, V_{GE} = 0, f = 1MHz$	—	720	—	pF
Switching Time	Rise Time	Inductive Load $V_{CC} = 300V, I_C = 10A$ $V_{GG} = \pm 15V, R_G = 100\Omega$ (Note 1)	—	0.12	—	$\mu s$
	Turn-On Time		—	0.40	—	
	Fall Time		—	0.15	0.30	
	Turn-Off Time		—	0.40	—	
Peak Forward Voltage	$V_F$	$I_F = 10A, V_{GE} = 0$	—	—	2.0	V
Reverse Recovery Time	$t_{rr}$	$I_F = 10A, di/dt = -100A/\mu s$	—	—	200	ns
Thermal Resistance (IGBT)	$R_{th(j-c)}$	—	—	—	2.08	°C/W
Thermal Resistance (Diode)	$R_{th(j-c)}$	—	—	—	3.76	°C/W

(Note 1) Switching time measurement circuit and input/output waveforms



Switching loss measurement waveforms

